

V1.1 Datasheet

N-Channel 30V MOSFET

FEATURES

- ●Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

PRODUCTY SUMMARY					
V_{DS}	R _{DS(on)} (mΩ) Max				
30	12	@V _{GS} =10.0V			
30	17	@V _{GS} =4.5V			

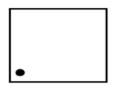
Application

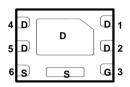
- ●Portable Devices
- ■Consumer Electronics

Mechanical

●Case:DFN2020 Package

DFN2020 Pin Configuration (Top View)





Internal Schematic Diagram

Packing Information

Package	Packing
DFN2020	3Kpcs/ 7"Reel



Maximum Ratings (T _A =25°C unless otherwise specified)						
Parameter	Symbol	Limit	Unit			
DrainSource Voltage	V _{DS}	30	V			
GateSource Voltage	V _{GS}	±20	V			
Continuous Drain Current 1)	I _D	12	А			
Maximum Power Dissipation	P _D	1.9	W			
Pulsed Drain Current 2)	I _{DM}	48	А			
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C			

Typical Thermal Resistance					
Parameter	Symbol	Limit	Unit		
JunctiontoAmbient Thermal Resistance 3)	$R_{\theta JA}$	62.5	°C/W		

Note:

- 1. Fused current that based on wire numbers and diameter
- 2. Repetitive Rating: Pulse width limited by the maximum junction temperature
- 3. 1-in2 2oz Cu PCB board



Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Cumb al	Test Condition	Limits			l lmit
Characteristics	Symbol		Min	Тур	Max	Unit
		Static				
DrainSource Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.00	1.20	3.00	V
DrainSource OnState Resistance	R _{DS(on)}	V_{GS} =10V, I_D =12A	-	7	12	mΩ
DrainSource OnState Resistance	R _{DS(on)}	V_{GS} =4.5V, I_{D} =10A	-	10	17	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	uA
GateSource Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA

DrainSource Diode						
Maximum Continuous Body Diode Forward Current	I _S	-	-	-	1.2	Α
Diode Forward Voltage	V_{SD}	I _S =1.0A, V _{GS} =0V	-	-	1.5	V

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

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Package Outline Dimensions (inches and millimeters)

	DF	N202	20		2,000±0,050 ——————————————————————————————————
		Dimei	nsions		<u> </u>
SYMBOL	Millim	neters	Inc	hes	
	Min	Max	Min	Max	2000+0.050 T/DFN
Α	0.70	0.80	0.39	0.41	2.000±0.050 (2 × 2) — 0 6 L PN H1 DOT BY HARKING 0.790±0.050 MIN 0.790±0.050 MIN 0.200 MIN 0.200 MIN 0.300±0.050 0.250±0.050 BOTTOM VIEW

Marking Information



AAAA = Product number

XXXX = Tracking number

Third line = Pin1 Point

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